

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	26	"275638"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/11 14:01
L2	4	"275638" and adachi	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/11 14:01
L3	9	JP-63093150-\$ or JP-61078138-\$ or JP-02031464-\$ or US-6809349-\$ or JP-04096337-\$ or JP-04101432-\$ or JP-02281634-\$ or US-6638825-\$ or JP-01128575-\$	US-PGPUB; USPAT; JPO	OR	ON	2006/03/11 14:01
L4	253	(thin adj film adj transistor or tft) and amorphous adj silicon WITH buffer	USPAT	OR	ON	2006/03/11 14:01
L5	7428	"117"/\$3.ccls.	USPAT	OR	ON	2006/03/11 14:01
L6	3968	(thin adj film adj transistor or tft) and amorphous adj silicon and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 14:01
L7	7021	(Park-Kee\$ or Yoo-J\$ or Han-M\$). in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 14:01
L8	8730	(257/347,350,390,40,51,57,59,66,72).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/03/11 14:01
L9	3953	L8 and (tft thin adj film adj transistor)	US-PGPUB; USPAT	OR	OFF	2006/03/11 14:01
L10	1037	L9 and buffer	US-PGPUB; USPAT	OR	OFF	2006/03/11 14:01
L12	29685	gate adj (insulator insulating insulation insulated insulate oxide) WITH thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 14:01

EAST Search History

L14	25	"4,767,723"	US-PGPUB; USPAT	OR	ON	2006/03/11 14:01
L15	742	"5837619" "5492843" (adachi and tft)	US-PGPUB; USPAT	OR	OFF	2006/03/11 14:01
L16	37747	gate insulating and gate electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/11 14:01
L17	21	(buffer near conductive) adj film	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/11 14:01
L18	19	((("6777747") or ("6534788") or ("6528855") or ("6509234") or ("6396079") or ("6033941") or ("5510640") or ("5196717") or ("5173753") or ("5144401") or ("4715930") or ("4287661") or ("4035198") or ("20040173812") or ("20040084722") or ("20040005740") or ("20030122178") or ("20020054247") or ("6746904"))). PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/03/11 14:01
L19	8	(L18 or L3) and (hoon near kim or thin adj film adj transistor or tft)	US-PGPUB; USPAT; JPO	OR	ON	2006/03/11 14:01
L20	15	L4 and L5	USPAT	OR	ON	2006/03/11 14:01
L21	21	(thin adj film adj transistor or tft) and amorphous adj silicon and L7	USPAT	OR	ON	2006/03/11 14:01
L22	43	"4851363" not L8	US-PGPUB; USPAT	OR	OFF	2006/03/11 14:01
L23	3060	etch adj rate near4 (sin silicon si)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/11 14:01
L24	82	L23 and process near4 etching near4 silicon adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/11 14:01

EAST Search History

L25	17	"5,310,457"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/11 14:01
L26	132	hoon near kim	US-PGPUB; USPAT	OR	OFF	2006/03/11 14:01
L27	637	(etch etching etchant etched pattern patterned patterning) near4 buffer and (thin adj film adj transistor or tft)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/11 14:01
L28	1270	L6 and "257"/\$3.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 14:01
L29	3271	L6 and step not step adj for	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 14:01
L30	3060	etch adj rate near4 (sin silicon si)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/11 14:01
L31	23	"275,638"	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/03/11 14:01
L32	3	(US-20040211356-\$).did. or (US-5985704-\$ or US-4949141-\$). did.	US-PGPUB; USPAT	OR	OFF	2006/03/11 14:01
L33	3	L32 and (thick thicker thickest thickened thicken thickness thin thinner) with (oxide nitride insulator insulating insulated)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2006/03/11 14:01